

# Jukka Viheriälä

## List of Publications by Year in descending order

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20  
papers

216  
citations

1163117

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996975

15  
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all docs

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docs citations

20  
times ranked

173  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Hybrid silicon photonics DBR laser based on flip-chip integration of GaSb amplifiers and $\lambda$ -scale SOI waveguides. Optics Express, 2022, 30, 24995.       | 3.4 | 11        |
| 2  | High-Power 1.5 $\mu$ m Tapered Distributed Bragg Reflector Laser Diodes for Eye-Safe LIDAR. IEEE Photonics Technology Letters, 2020, 32, 1249-1252.              | 2.5 | 4         |
| 3  | GaSb diode lasers tunable around 2.6 $\mu$ m using silicon photonics resonators or external diffractive gratings. Applied Physics Letters, 2020, 116, .          | 3.3 | 21        |
| 4  | High Peak Power Laser Diodes for Eye Safe LIDAR with Integrated Wavelength Locking Element. , 2019, , .  |     | 0         |
| 5  | Design Strategies for Power Scaling of GaSb-Based Superluminescent Diodes for 2 $\mu$ – 3 $\mu$ m Wavelength Range. , 2019, , .                                  |     | 0         |
| 6  | GaSb-Based 2.55 $\mu$ m External Cavity Diode Lasers Employing Ruled Diffraction Gratings and External Silicon Photonics Vernier Reflectors. , 2019, , .         |     | 0         |
| 7  | High Power 1.5 $\mu$ m Pulsed Laser Diode With Asymmetric Waveguide and Active Layer Near p-cladding. IEEE Photonics Technology Letters, 2019, 31, 1635-1638.    | 2.5 | 14        |
| 8  | High power GaInNAs superluminescent diodes emitting over 400 mW in the 1.2 $\mu$ m wavelength range. Applied Physics Letters, 2019, 115, .                       | 3.3 | 5         |
| 9  | High-power single mode GaSb-based 2 $\mu$ m superluminescent diode with double-pass gain. Applied Physics Letters, 2019, 115, .                                  | 3.3 | 7         |
| 10 | High-power 1.5 $\mu$ m laser diodes for LIDAR applications. , 2019, , .  |     | 3         |
| 11 | GaSb superluminescent diodes with broadband emission at 2.55 $\mu$ m. Applied Physics Letters, 2018, 112, .  | 3.3 | 15        |
| 12 | High-Power 1.5- $\mu$ m Broad Area Laser Diodes Wavelength Stabilized by Surface Gratings. IEEE Photonics Technology Letters, 2018, 30, 1870-1873.               | 2.5 | 6         |
| 13 | Low loss GaInNAs/GaAs gain waveguides with U-bend geometry for single-facet coupling in hybrid photonic integration. Applied Physics Letters, 2018, 113, 041104. | 3.3 | 8         |
| 14 | Multi-wavelength mid-IR light source for gas sensing. Proceedings of SPIE, 2017, , .   | 0.8 | 6         |
| 15 | High-power 1550 nm tapered DBR laser diodes for LIDAR applications. , 2017, , .  |     | 5         |
| 16 | High-Power 1180-nm GaInNAs DBR Laser Diodes. IEEE Photonics Technology Letters, 2017, 29, 2023-2026.   | 2.5 | 7         |
| 17 | High power (60 mW) GaSb-based 1.9 $\mu$ m superluminescent diode with cavity suppression element. Applied Physics Letters, 2016, 109, .                          | 3.3 | 21        |
| 18 | High Spectral Purity High-Power GaSb-Based DFB Laser Fabricated by Nanoimprint Lithography. IEEE Photonics Technology Letters, 2016, 28, 1233-1236.              | 2.5 | 17        |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 19 | High-power temperature-stable GaInNAs distributed Bragg reflector laser emitting at 1180â€™nm. Optics Letters, 2016, 41, 657.               | 3.3 | 15        |
| 20 | Applications of UV-nanoimprint soft stamps in fabrication of single-frequency diode lasers. Microelectronic Engineering, 2009, 86, 321-324. | 2.4 | 51        |